

	Type	Hits	Search Text
1	BRS	33	(variable adj capacitance adj capacitor).ti.
2	BRS	33	(variable adj capacitance adj capacitor).ti.
3	BRS	17	(variable adj capacitance adj capacitor) and (MOS)
4	BRS	427	(variable adj capacitor) and (MOS)
5	BRS	1278	(variable adj capacitor).ti.
6	BRS	427	(variable adj capacitor) and (MOS)
7	IS&R	1986	(257/296).CCLS.
8	BRS	10428	LDD
9	BRS	56	(LDD) and (transparent adj insulating adj substrate)
10	BRS	27	(LDD) and (transparent adj insulating adj substrate) and (ion adj implantation)
11	BRS	3872	(LDD) and (transparent adj insulating adj substrate) and (ion adj implantation) adn
12	BRS	27	(LDD) and (transparent adj insulating adj substrate) and (ion adj implantation) and ((insulating or insulation or insulator))
13	BRS	4	(LDD) and ((transparent adj insulating adj substrate) with ((poly-silicon) or (polysilicon))) and (ion adj implantation) and ((insulating or insulation or insulator))
14	BRS	27799	thin adj film adj transistor
15	BRS	0	(thin adj film adj transistor) and (second adj ion adj implantation) and ((barrier adj layer) with (insulating adj layer))

	<b>DBs</b>	<b>Time Stamp</b>	<b>Comments</b>	<b>Error Definition</b>
1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/15 13:38		
2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 11:30		
3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 11:58		
4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 11:58		
5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 11:59		
6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 11:59		
7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/17 11:39		
8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/15 13:55		
9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/15 13:57		
10	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/15 13:57		
11	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/15 13:57		
12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/15 14:18		
13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/15 15:35		
14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/15 15:36		
15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/15 15:38		

<b>Errors</b>	
1	0
2	0
3	0
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13	0
14	0
15	0

	Type	Hits	Search Text
16	BRS	13	(thin adj film adj transistor) and (ion adj implantation) and ((barrier adj layer) with (insulating adj layer))
17	BRS	4996	capacitor with trench
18	BRS	1878	(capacitor with trench) and ((MOS or (field adj effect)))
19	IS&R	438	(257/510).CCLS.
20	IS&R	71	(257/510).CCLS.
21	BRS	1273	test adj socket
22	IS&R	4854	(257/672,674,676,735,773,786).CCLS.
23	BRS	24021	test adj device
24	BRS	9570	(test adj device).ti.
25	BRS	66	((test adj device) with chip).ti.
26	BRS	1734	(test adj device) and chip

	<b>DBs</b>	<b>Time Stamp</b>	<b>Comments</b>	<b>Error Definition</b>
16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 17:28		
17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 17:29		
18	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 17:31		
19	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/17 12:35		
20	JPO	2002/06/17 12:35		
21	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/18 12:21		
22	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 11:38		
23	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 12:33		Query aborted.
24	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 12:36		
25	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 12:36		
26	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 12:41		

<b>Errors</b>	
16	0
17	0
18	0
19	0
20	0
21	0
22	0
23	1
24	0
25	0
26	0